

Abstract of the Disclosure

The present invention provides a semiconductor memory device and a fabrication method capable of preventing the contact between a dielectric layer of a capacitor and a diffusion barrier. The plug comprises a diffusion barrier layer and a seed layer for forming a lower electrode of a capacitor. Accordingly, it is possible to prevent the dielectric layer being contacted with the diffusion barrier, whereby the leakage current may be reduced, and the capacitance of the capacitor may be increased.